



40V 175°C N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	Qg Typ	I _D T _C = +25°C (Note 10)
40V	3.2mΩ @ V _{GS} = 10V	68.6nC	100A

Features

- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching Ensures More Reliable and Robust End Application
- Low R_{DS(ON)} Minimizes Power Losses
- Low Qg Minimizes Switching Losses
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Engine Management Systems
- Body Control Electronics
- DC/DC Converters

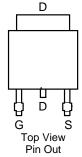
Mechanical Data

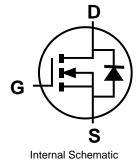
- Case: TO252 (DPAK)
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.33 grams (Approximate)





Top View





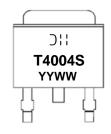
Ordering Information (Note 5)

Part Number	Case	Packaging
DMTH4004SK3Q-13	TO252 (DPAK)	2,500/Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/product_compliance_definitions.html.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



T4004S = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 16 = 2016)
WW = Week Code (01 to 53)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V_{DSS}	40	V	
Gate-Source Voltage	V_{GSS}	±20	V	
Continuous Drain Current (Note 7)	T _C = +25°C (Note 10)	I _D	100	А
, , ,	T _C = +100°C]	100	
Maximum Body Diode Forward Current (Note 7)	Is	100	Α	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	160	Α	
Avalanche Current, L=0.2mH	I _{AS}	40	Α	
Avalanche Energy, L=0.2mH	E _{AS}	160	mJ	

Thermal Characteristics

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 6) $T_A = +25^{\circ}C$		P_{D}	3.9	W
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	38	°C/W	
Total Power Dissipation (Note 7) $T_C = +25^{\circ}C$		P_{D}	180	W
Thermal Resistance, Junction to Case (Note 7)	R _θ JC	0.8	°C/W	
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +175	°C	

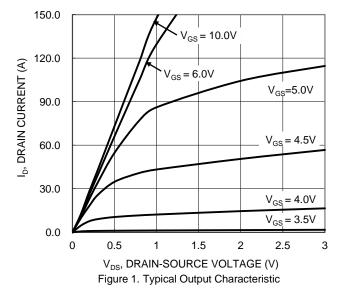
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

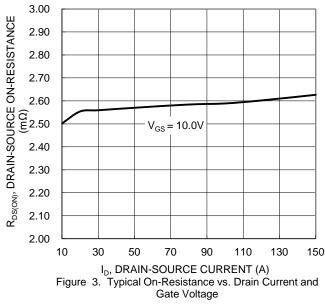
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV _{DSS}	40	_	_	V	$V_{GS} = 0V$, $I_D = 1mA$	
Zero Gate Voltage Drain Current	I _{DSS}		_	1	μA	$V_{DS} = 32V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}		_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V _{GS(TH)}	2	_	4	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
Static Drain-Source On-Resistance	R _{DS(ON)}		2.6	3.2	mΩ	$V_{GS} = 10V, I_D = 90A$	
Diode Forward Voltage	V_{SD}		0.9	1.2	V	$V_{GS} = 0V, I_{S} = 20A$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	Ciss	_	4,305	_		V _{DS} = 25V, V _{GS} = 0V, f = 1MHz	
Output Capacitance	Coss		1,441	_	pF		
Reverse Transfer Capacitance	Crss		102	_			
Gate Resistance	R_G		0.77	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge	Q_g	_	68.6	_		V _{DS} = 20V, I _D = 90A, V _{GS} = 10V	
Gate-Source Charge	Qgs	_	16.8	_	nC		
Gate-Drain Charge	Q_{gd}	_	14.2	_			
Turn-On Delay Time	t _{D(ON)}	_	9.5	_		$V_{DD} = 20V, V_{GS} = 10V,$ $I_{D} = 90A, R_{G} = 3.5\Omega$	
Turn-On Rise Time	t _R	_	6.7	_			
Turn-Off Delay Time	t _{D(OFF)}	_	26.4	_	ns		
Turn-Off Fall Time	t _F	_	8.1	_			
Body Diode Reverse Recovery Time	t _{RR}	_	52.4	_	ns	L 500 di/dt 4000///-	
Body Diode Reverse Recovery Charge	Q_{RR}	_	78.2	_	nC	I _F = 50A, di/dt = 100A/μs	

Notes: 6. Device mounted with exposed drain pad on 25mm by 25mm 2oz copper on a single- sided 1.6mm FR-4 PCB; device is measured under still air conditions whilst operating in a steady state.

- 7. Thermal resistance from junction to solder point (on the exposed drain pin).
- 8. Short duration pulse test used to minimize self-heating effect.
- 9. Guaranteed by design. Not subject to production testing.
- 10. Package limited.







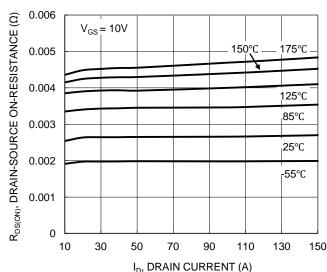
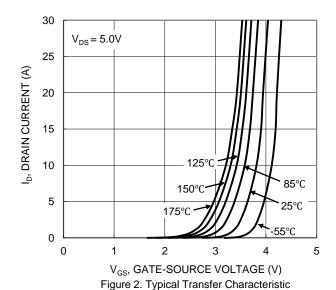
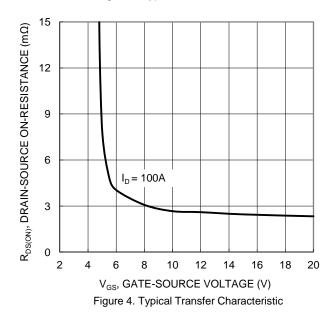
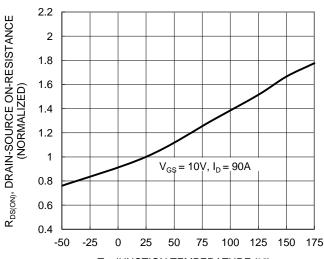


Figure 5. Typical On-Resistance vs. Drain Current and Temperature







T_J, JUNCTION TEMPERATURE (°C)
Figure 6. On-Resistance Variation with Temperature



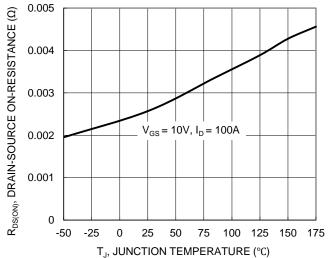


Figure 7. On-Resistance Variation with Temperature

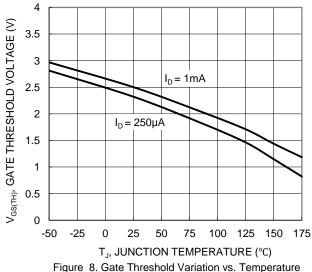


Figure 8. Gate Threshold Variation vs. Temperature

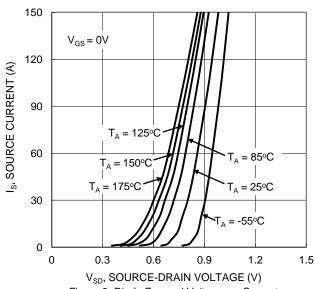
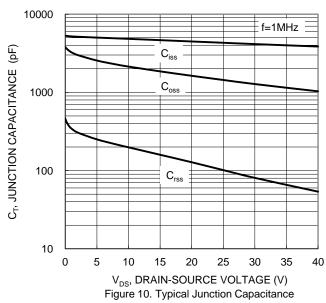
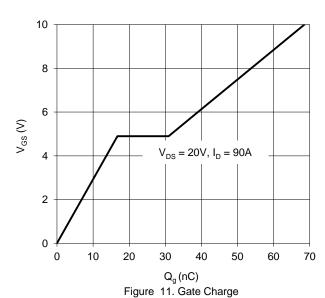


Figure 9. Diode Forward Voltage vs. Current



1200 1000 $I_{AS} = 22.5A$ 800 EAS (mJ) $I_{AS} = 45A$ 600 $1_{AS} = 90A$ 400 200 0 <u></u> 25 50 75 100 150 Tj(℃)

Figure 12 EAS vs Tj



175



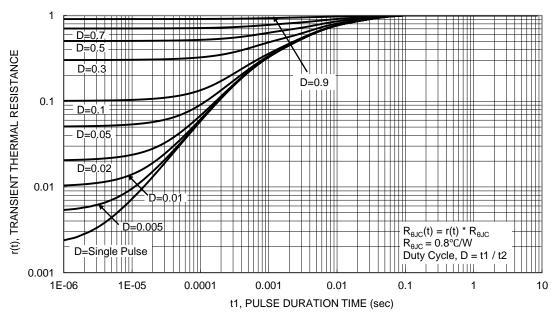


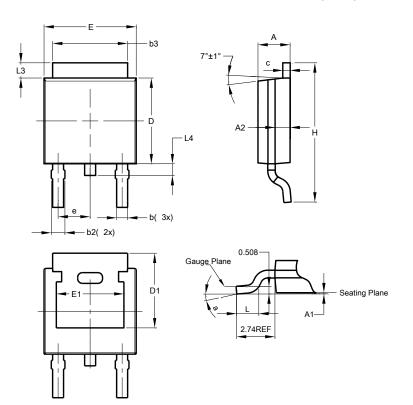
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO252 (DPAK)

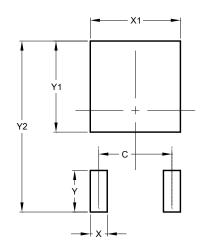


TO252 (DPAK)					
Dim	Min	Max	Тур		
Α	2.19	2.39	2.29		
A 1	0.00	0.13	0.08		
A2	0.97	1.17	1.07		
q	0.64	0.88	0.783		
b2	0.76	1.14	0.95		
b3	5.21	5.46	5.33		
С	0.45	0.58	0.531		
D	6.00	6.20	6.10		
D1	5.21	-	-		
е	-	-	2.286		
Е	6.45	6.70	6.58		
E1	4.32	-	-		
H	9.40	10.41	9.91		
L	1.40	1.78	1.59		
L3	0.88	1.27	1.08		
L4	0.64	1.02	0.83		
а	0°	10°	-		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO252 (DPAK)



Dimensions	Value (in mm)		
С	4.572		
Х	1.060		
X1	5.632		
Y	2.600		
Y1	5.700		
Y2	10.700		



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